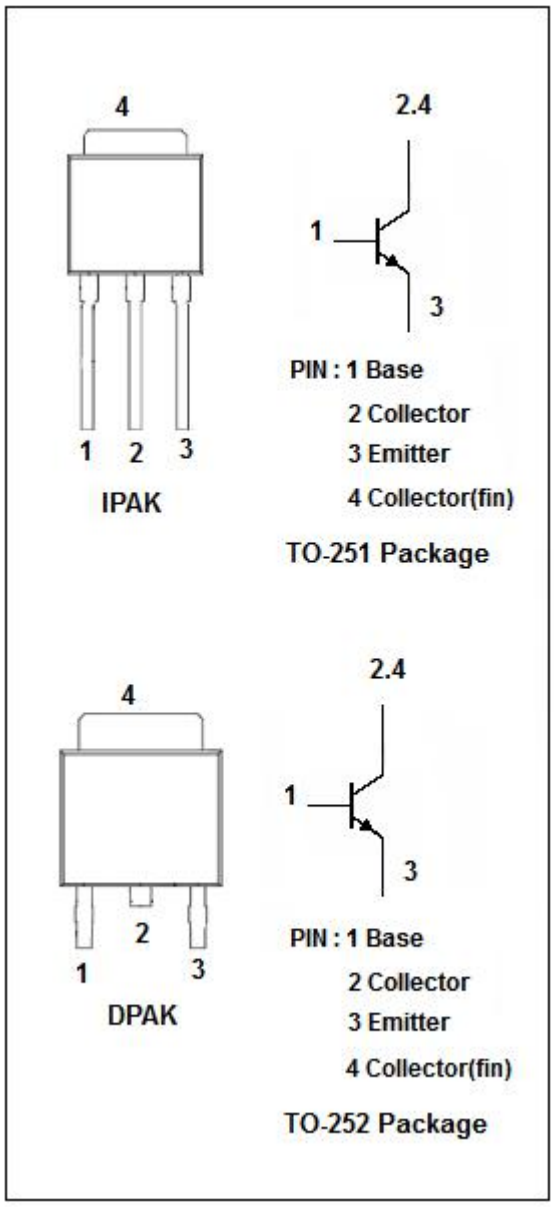
isc Silicon NPN Power Transistor 3DA752

DESCRIPTION

- Low $V_{CE(sat)}$
- Small and slim package
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power dissipation



ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2	A
P_C	Collector Power Dissipation	1.2	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 2A; I_B= 200mA			0.8	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 1.5A; I_B= 30mA			2.0	V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 100uA; I_B= 0	40			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; I_B= 0	30			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	5			V
I_{CBO}	Collector Cutoff Current	V_{CB}= 40V; I_E= 0			0.1	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.1	μA
h_{FE}	DC Current Gain	I_C= 0.5A; V_{CE}= 2V	100		400	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f= 1.0MHz		13		pF
f_T	Current-Gain—Bandwidth Product	I_C= 500mA; V_{CE}= 5V		120		MHz

◆ **h_{FE} Classifications**

O	Y	G
100-200	160-320	200-400

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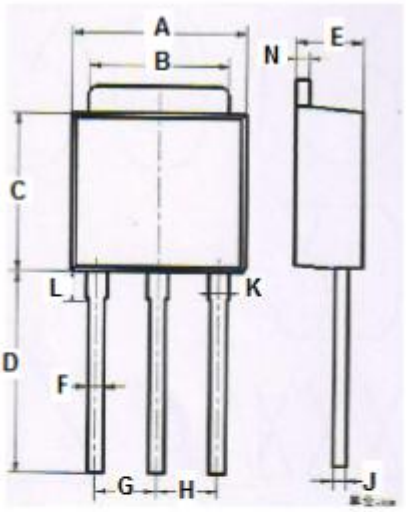
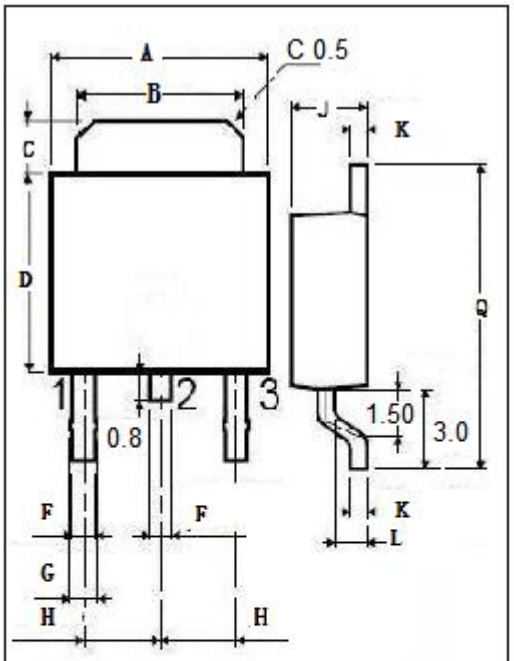
Outline Drawing



DIM	mm MIN	MAX
A	6.40	6.48
B	5.10	5.50
C	5.80	6.20
D	9.20	9.60
E	2.20	2.40
F	0.50	0.70
G	2.09	2.49
H	2.09	2.49
J	0.40	0.60
K	0.70	0.90
L	1.60	2.00
N	0.40	0.60



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1